NJD35N04G

NPN Darlington Power Transistor

This high voltage power Darlington has been specifically designed for inductive applications such as Electronic Ignition, Switching Regulators and Motor Control.

Features

- Exceptional Safe Operating Area
- High V_{CE}; High Current Gain
- These are Pb−Free Devices

Benefits

- Reliable Performance at Higher Powers
- Designed for Inductive Loads
- Very Low Current Requirements

Applications

- Internal Combustion Engine Ignition Control
- Switching Regulators
- Motor Controls
- Light Ballast
- Photo Flash

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector−Emitter Sustaining Voltage	V_{CEO}	350	Vdc
Collector−Base Breakdown Voltage	V_{CBO}	700	Vdc
Collector−Emitter Breakdown Voltage	V_{CES}	700	Vdc
Emitter−Base Voltage	V_{EBO}	5.0	Vdc
Collector Current − Continuous Peak	I_C I_{CM}	4.0 8.0	Adc
Base Current	I_B	0.5	Adc
Total Power Dissipation @ T_C = 25°C Derate above 25°C	P_D	45 0.36	W W/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

THERMAL CHARACTERISTICS

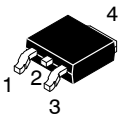
Characteristic	Symbol	Value	Unit
Thermal Resistance − Junction−to−Case Junction−to−Ambient	$R_{\theta JC}$ $R_{\theta JA}$	2.78 71.4	°C/W

ON Semiconductor®

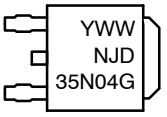
http://onsemi.com

DARLINGTON POWER TRANSISTORS 4 AMPERES 350 VOLTS 45 WATTS

MARKING DIAGRAM



DPAK
CASE 369C
STYLE 1



Y = Year
WW = Work Week
NJD35N04 = Device Code
G = Pb−Free Device

ORDERING INFORMATION

Device	Package	Shipping†
NJD35N04G	DPAK (Pb−Free)	75 Units / Rail
NJD35N04T4G	DPAK (Pb−Free)	2500/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector−Emitter Sustaining Voltage (I_C = 10 mA, L = 10 mH)	$V_{CEO(sus)}$	350	–	–	V
Collector Cutoff Current (V_{CE} = 500 V) (I_B = 0) (V_{CE} = 500 V, T_C = 125°C)	I_{CES}	– –	– –	50 250	μA
Collector Cutoff Current (V_{CE} = 250 V) (I_B = 0) (V_{CE} = 200 V, T_C = 125°C)	I_{CEO}	– –	– –	50 250	μA
Emitter Cutoff Current (V_{BE} = 5.0 Vdc)	I_{EBO}	–	–	5.0	μA
ON CHARACTERISTICS					
Collector−Emitter Saturation Voltage (I_C = 2.0 A, I_B = 20 mA) (I_C = 2.0 A, I_B = 20 mA 125°C)	$V_{CE(sat)}$	–	–	1.5	V
Base−Emitter Saturation Voltage (I_C = 2.0 A, I_B = 20 mA) (I_C = 2.0 A, I_B = 20 mA 125°C)	$V_{BE(sat)}$	–	–	2.0	V
Base−Emitter On Voltage (I_C = 2.0 A, V_{CE} = 2.0 V) (I_C = 2.0 A, V_{CE} = 2.0 V 125°C)	$V_{BE(on)}$	–	–	2.0	V
DC Current Gain (I_C = 2.0 A, V_{CE} = 2.0 V) (I_C = 4.0 A, V_{CE} = 2.0 Vdc)	h_{FE}	 2000 300	 – –	 – –	–
DYNAMIC CHARACTERISTICS					
Current−Gain − Bandwidth Product (I_C = 2.0 A, V_{CE} = 10 V, f = 1.0 MHz)	f_T	90	–	–	MHz
Output Capacitance (V_{CB} = 10 V, I_E = 0, f = 0.1 MHz)	C_{ob}	–	60	–	pF
SWITCHING CHARACTERISTICS					
V_{CC} = 12 V, V_{clamp} = 250 V, L = 4 mH I_C = 2 A, I_{B1} = 20 mA, I_{B2} = −20 mA	t_s t_f	– –	18 0.8	– –	μSec

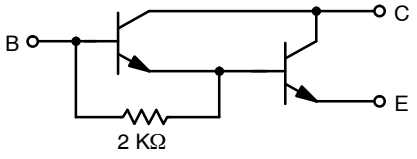


Figure 1. Darlington Circuit Schematic

TYPICAL CHARACTERISTICS

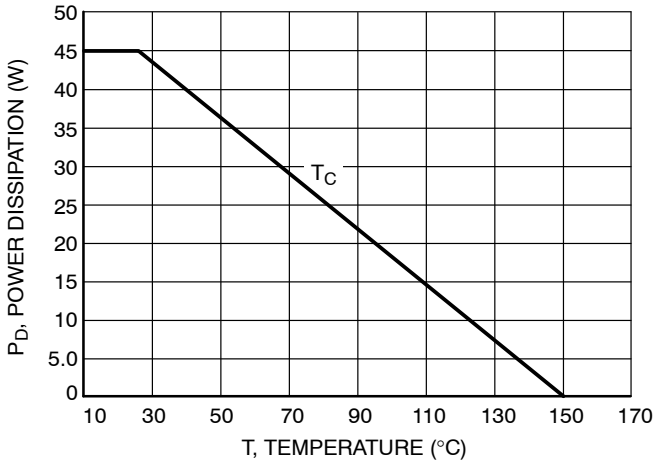


Figure 2. Power Derating

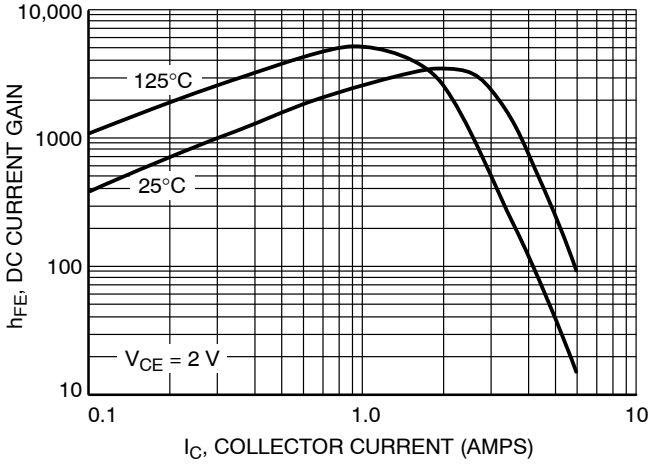


Figure 3. DC Current Gain

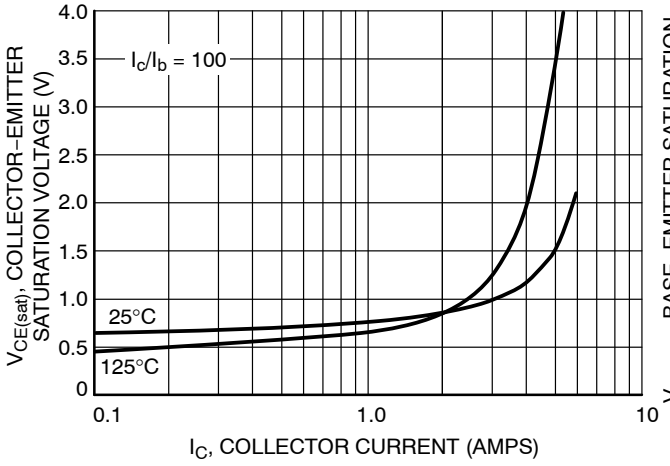


Figure 4. Collector−Emitter Saturation Voltage

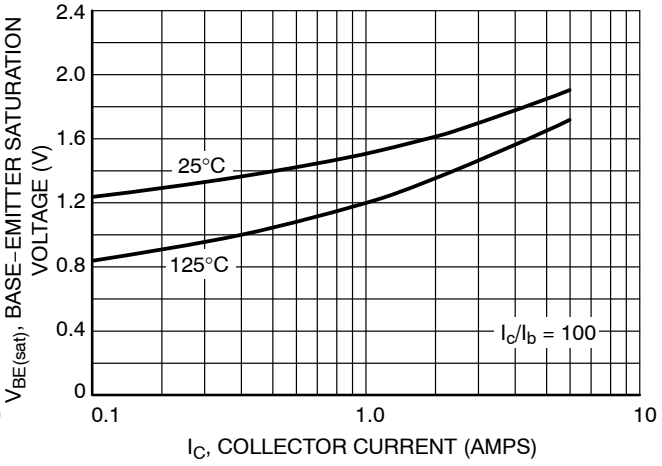


Figure 5. Base−Emitter Saturation Voltage

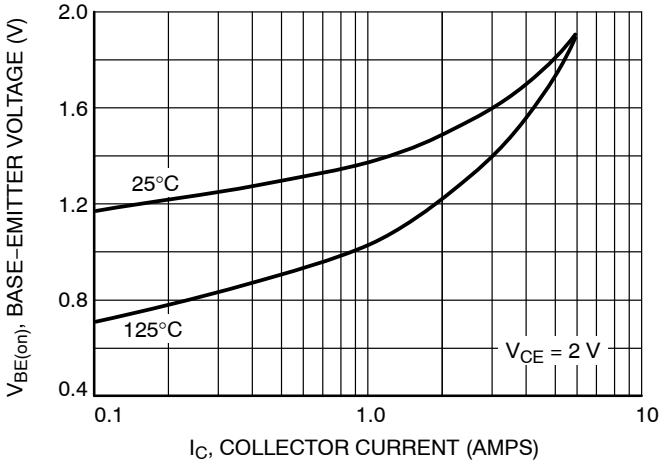


Figure 6. Base−Emitter Voltage

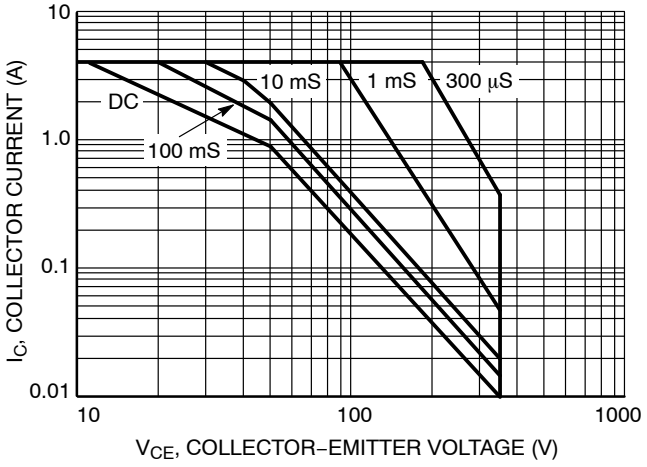
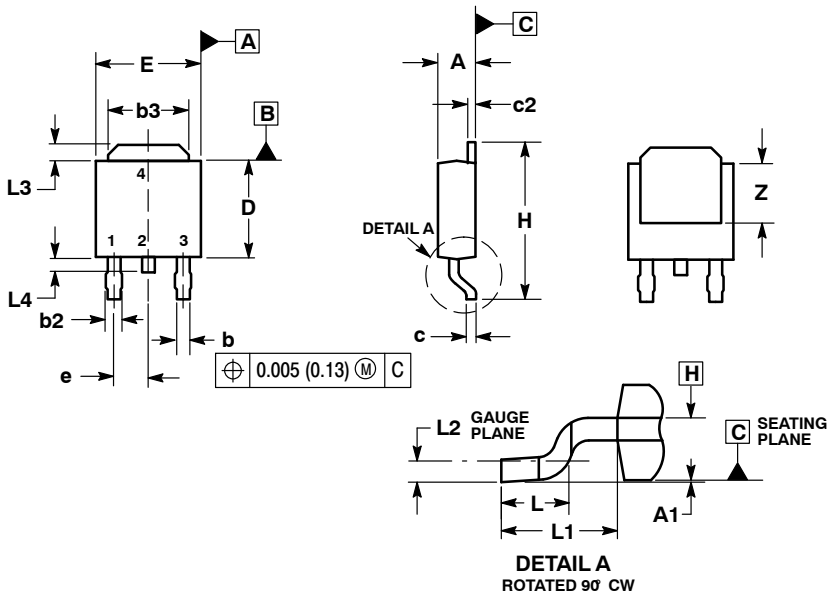


Figure 7. Forward Bias Safe Operating Area (FBSOA)

PACKAGE DIMENSIONS

DPAK
CASE 369C−01
ISSUE D

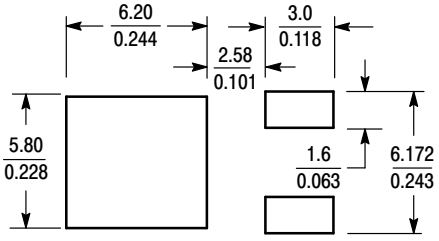


NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: INCHES.
3. THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS b3, L3 and Z.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.006 INCHES PER SIDE.
5. DIMENSIONS D AND E ARE DETERMINED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
6. DATUMS A AND B ARE DETERMINED AT DATUM PLANE H.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.086	0.094	2.18	2.38
A1	0.000	0.005	0.00	0.13
b	0.025	0.035	0.63	0.89
b2	0.030	0.045	0.76	1.14
b3	0.180	0.215	4.57	5.46
c	0.018	0.024	0.46	0.61
c2	0.018	0.024	0.46	0.61
D	0.235	0.245	5.97	6.22
E	0.250	0.265	6.35	6.73
e	0.090 BSC		2.29 BSC	
H	0.370	0.410	9.40	10.41
L	0.055	0.070	1.40	1.78
L1	0.108 REF		2.74 REF	
L2	0.020 BSC		0.51 BSC	
L3	0.035	0.050	0.89	1.27
L4	−−−	0.040	−−−	1.01
Z	0.155	−−−	3.93	−−−

STYLE 1:
PIN 1. BASE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

SOLDERING FOOTPRINT*



SCALE 3:1 $\left(\frac{\text{mm}}{\text{inches}}\right)$

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Literature Distribution Center for ON Semiconductor
P.O. Box 5163, Denver, Colorado 80217 USA
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Fax: 303−675−2176 or 800−344−3867 Toll Free USA/Canada
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